

Jiangxiaizi Lin

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Achieving Ultrahigh Carrier Mobility in Two-Dimensional Hole Gas of Black Phosphorus. <i>Nano Letters</i> , 2016, 16, 7768-7773.	9.1	242
2	Universal low-temperature Ohmic contacts for quantum transport in transition metal dichalcogenides. <i>2D Materials</i> , 2016, 3, 021007.	4.4	102
3	Even-odd layer-dependent magnetotransport of high-mobility Q-valley electrons in transition metal disulfides. <i>Nature Communications</i> , 2016, 7, 12955.	12.8	82
4	Intrinsic valley Hall transport in atomically thin MoS ₂ . <i>Nature Communications</i> , 2019, 10, 611.	12.8	77
5	Interaction effects and superconductivity signatures in twisted double-bilayer WSe ₂ . <i>Nanoscale Horizons</i> , 2020, 5, 1309-1316.	8.0	68
6	Spin-orbit-driven ferromagnetism at half moiré filling in magic-angle twisted bilayer graphene. <i>Science</i> , 2022, 375, 437-441.	12.6	61
7	van der Waals Epitaxial Growth of Atomically Thin Bi ₂ Se ₃ and Thickness-Dependent Topological Phase Transition. <i>Nano Letters</i> , 2015, 15, 2645-2651.	9.1	54
8	Effects of Hexagonal Boron Nitride Encapsulation on the Electronic Structure of Few-Layer MoS ₂ . <i>Journal of Physical Chemistry C</i> , 2019, 123, 14797-14802. <i>Odd-Integer Quantum Hall States and Giant Spin Susceptibility in</i> WSe_2 <i>Encapsulated by</i> MoS_2 <i>and</i> BN <i>Monolayers</i> . <i>Physical Review Letters</i> , 2017, 118, 067702.	3.1	42
9	Odd-Integer Quantum Hall States and Giant Spin Susceptibility in WSe_2 -Type Few-Layer MoS_2 Encapsulated by BN Monolayers. <i>Physical Review Letters</i> , 2017, 118, 067702.	7.8	37
10	Determining Interaction Enhanced Valley Susceptibility in Spin-Valley-Locked MoS ₂ . <i>Nano Letters</i> , 2019, 19, 1736-1742.	9.1	35
11	Ambipolar quantum transport in few-layer black phosphorus. <i>Physical Review B</i> , 2017, 96, .	3.2	26
12	Detection of interlayer interaction in few-layer graphene. <i>Physical Review B</i> , 2015, 92, .	3.2	22
13	A fast transfer-free synthesis of high-quality monolayer graphene on insulating substrates by a simple rapid thermal treatment. <i>Nanoscale</i> , 2016, 8, 2594-2600.	5.6	20
14	Bridging the gap between atomically thin semiconductors and metal leads. <i>Nature Communications</i> , 2022, 13, 1777.	12.8	17
15	Probing the electronic states and impurity effects in black phosphorus vertical heterostructures. <i>2D Materials</i> , 2016, 3, 015012.	4.4	16
16	Negative compressibility in graphene-terminated black phosphorus heterostructures. <i>Physical Review B</i> , 2016, 93, .	3.2	10
17	Charge density wave phase transition on the surface of electrostatically doped multilayer graphene. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	4
18	Fluctuation-induced tunneling conduction in iodine-doped bilayer graphene. <i>Journal of Applied Physics</i> , 2018, 123, 244302.	2.5	2